



UHBS30-1

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI UHBS30-1 is Designed for

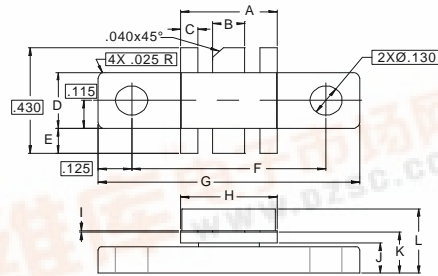
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CB0}	50 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	100 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .230 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

ORDER CODE: ASI10670

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	30			V
BV_{CES}	I _C = 50 mA R _{BE} = 10 Ω	50			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CB0}	V _{CE} = 15 V			5	mA
I_{CES}	V _{CE} = 24 V			10	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		---	---
C_{ob}	V _{CB} = 25 V f = 1.0 MHz			50	pF
P_G	V _{CE} = 24 V P _{OUT} = 30 W f = 900 GHz	7.5			dB
η_C			55		%

